

Silicon NPN Power Transistors

2SC2292

DESCRIPTION

- With TO-3 package
- High speed ,high voltage

APPLICATIONS

- For high speed ,high voltage switching and DC-DC converter application

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

MAXIMUM RATINGS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		8	A
P_T	Total power dissipation	$T_{mb} \leq 25^\circ C$	80	W
T_j	Junction temperature		150	$^\circ C$
T_{stg}	Storage temperature		-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.25	$^\circ C/W$

Silicon NPN Power Transistors**2SC2292****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA$; $I_B=0$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA$; $I_E=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A$; $I_B=0.8A$			0.8	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4A$; $I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=500V$; $I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V$; $I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=4A$; $V_{CE}=2V$	15			

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PACKAGE OUTLINE

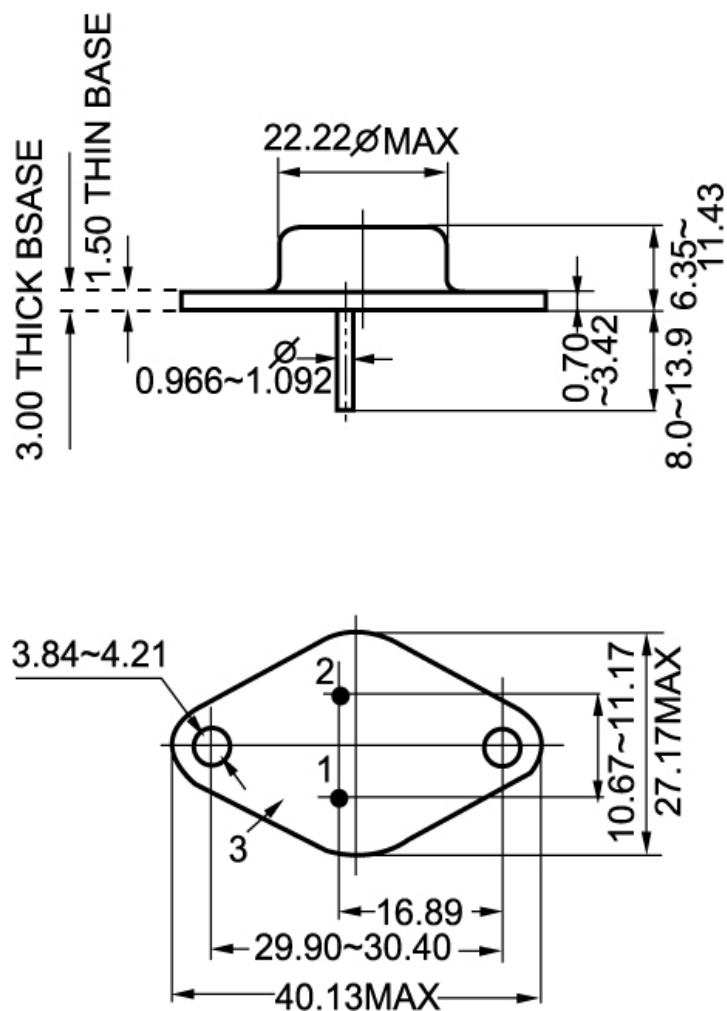


Fig.2 Outline dimensions